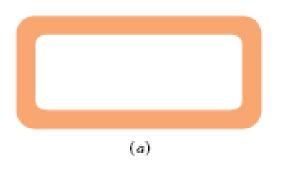
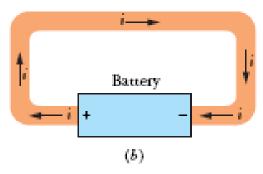
## Welcome to the Physics class



**Principles of Physics II** 

# Lecture 14

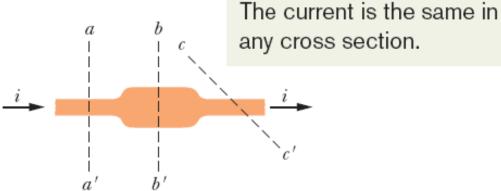




(a) A loop of copper in Fig. 26-1 electrostatic equilibrium. The entire loop is at a single potential, and the electric field is zero at all points inside the copper. (b) Adding a battery imposes an electric potential difference between the ends of the loop that are connected to the terminals of the battery. The battery thus produces an electric field within the loop, from terminal to terminal, and the field causes charges to move around the loop. This movement of charges is a current i.

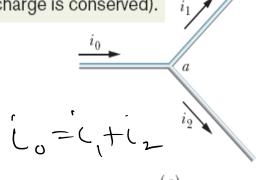
## CURRENT AND RESISTANCE

**Fig. 26-2** The current *i* through the conductor has the same value at planes aa',bb', and cc'.



Law = 
$$\frac{V}{t}$$
 Also  $dq = idt$   
 $v = \int dq = \int idt$  wint = And  
 $direction N = urrowt$ 

The current into the junction must equal the current out (charge is conserved).

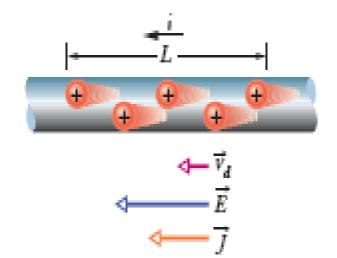


**Current density** J's a restor "II" to the drift retaining the charse. Current through an element of area dia 1. - $\frac{di}{di} = J \cdot dA$   $i = J \cdot dA = J \cdot dA$   $J = \frac{i}{A} \quad \text{ roughton } J \cdot dA = J \cdot dA$ 

#### **Drift Velocity**

Fig. 26-5 Positive charge carriers drift at speed  $v_d$  in the direction of the applied electric field  $\vec{E}$ . By convention, the direction of the current density  $\vec{J}$  and the sense of the current arrow are drawn in that same direction.

Current is said to be due to positive charges that are propelled by the electric field.



t Variet ~ 10 to 10 m/s t Variet ~ 10 rolser

Random molion of elichans in a conductor when there is no current flowing

#### **Drift Velocity** Contd.

Current is said to be due to positive charges that are propelled by the electric field.

$$c = \frac{Q}{L} = \frac{enal}{L}$$

Assume 5 in uniform airriss A

No. 18 charse corriers in light L of the coolings

 $m \times (AL)$ 

done carrivam that a herrer in

Q= ex(nAL) possis

through any x-getton of Ihr contrator in t sec.

## Resistance and Resistivity

Current is driven by a potential difference.

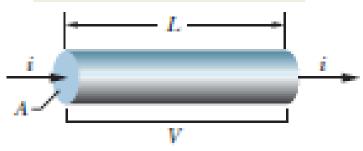
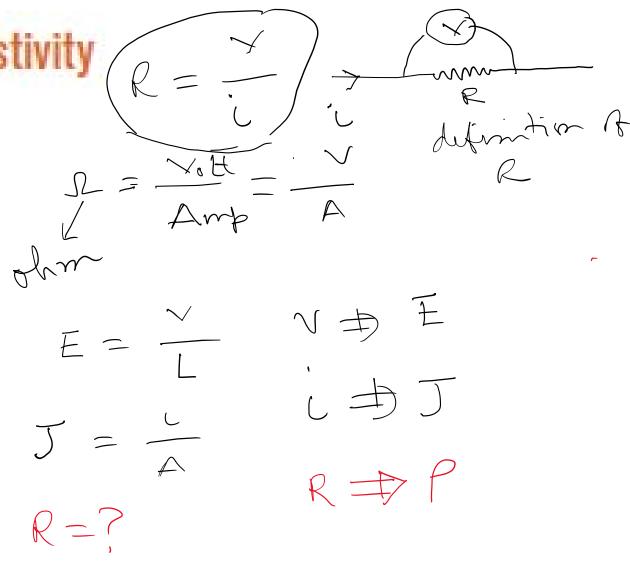


Figure 26-9 A potential difference V is applied between the ends of a wire of length L and cross section A, establishing a current i.



R= Resistance of a resenter

f = Resistance of a resistanc We before  $f = \frac{E}{J}$  J = fJNow, we define conductivity  $\sigma = \frac{1}{p} \left( df + conductivity \right)$ J= E = DE

Principosiokic Ohm's law

J= E = DE

#### Calculating Resistance from Resistivity

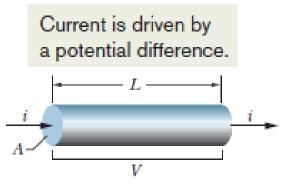


Figure 26-9 A potential difference V is applied between the ends of a wire of length L and cross section A, establishing a current i.

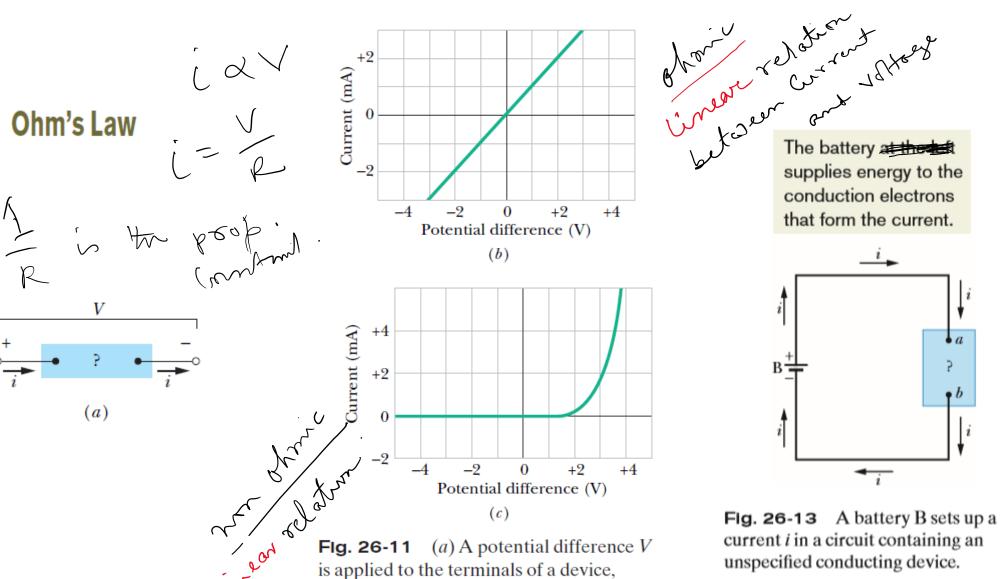
Africal  $\Rightarrow$   $f = \frac{L}{5} = \frac{\sqrt{L}}{\sqrt{A}} \Rightarrow \frac{$ 

### Table 26-1 Resistivities of Some Materials at Room Temperature (20°C)

Material	Resistivity, $\rho$ $(\Omega \cdot m)$	Temperature Coefficient of Resistivity α (K <sup>-1</sup> )
	Typical Metals	;
Silver	$1.62 \times 10^{-8}$	$4.1 \times 10^{-3}$
Copper	$1.69 \times 10^{-8}$	$4.3 \times 10^{-3}$
Gold	$2.35 \times 10^{-8}$	$4.0 \times 10^{-3}$
Aluminum	$2.75 \times 10^{-8}$	$4.4 \times 10^{-3}$
Manganin <sup>a</sup>	$4.82 \times 10^{-8}$	$0.002 \times 10^{-3}$
Tungsten	$5.25 \times 10^{-8}$	$4.5 \times 10^{-3}$
Iron	$9.68 \times 10^{-8}$	$6.5 \times 10^{-3}$
Platinum	$10.6  imes 10^{-8}$	$3.9 \times 10^{-3}$
	Typical Semice	onductors
Silicon, pure	$2.5 \times 10^{3}$	$-70 \times 10^{-3}$
Silicon, n-type <sup>b</sup>	$8.7 \times 10^{-4}$	
Silicon, p-type <sup>c</sup>	$2.8 \times 10^{-3}$	
Glass	Typical Insula 10 <sup>10</sup> – 10 <sup>14</sup>	tors
Fused quartz	~1016	. ) .



Resistance is a property of an object. Resistivity is a property of a material.



establishing a current i. (b) A plot of current i versus applied potential difference Vwhen the device is a 1000  $\Omega$  resistor. (c) A plot when the device is a semiconducting

*pn* junction diode.

current i in a circuit containing an unspecified conducting device.

### **Power in Electric Circuits**

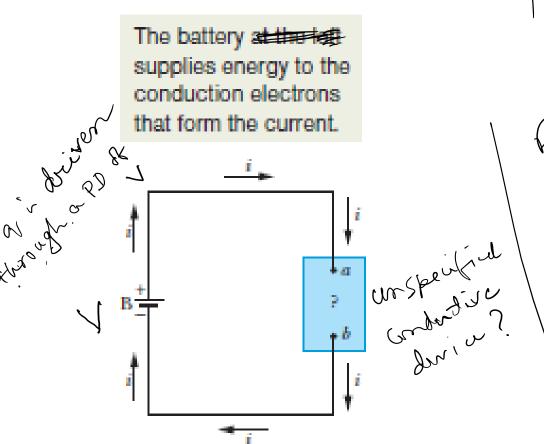


Figure 26-13 A battery B sets up a current i in a circuit containing an unspecified conducting device.

Current An electric current i in a conductor is defined by

$$i = \frac{dq}{dt}. (26-1)$$

Here dq is the amount of (positive) charge that passes in time dt through a hypothetical surface that cuts across the conductor. By convention, the direction of electric current is taken as the direction in which positive charge carriers would move. The SI unit of electric current is the **ampere** (A): 1 A = 1 C/s.

**Current Density** Current (a scalar) is related to **current density**  $\vec{J}$  (a vector) by

 $i = \int \vec{J} \cdot d\vec{A}, \qquad (26-4)$ 

where  $d\vec{A}$  is a vector perpendicular to a surface element of area dA and the integral is taken over any surface cutting across the conductor.  $\vec{J}$  has the same direction as the velocity of the moving charges if they are positive and the opposite direction if they are negative.

**Drift Speed of the Charge Carriers** When an electric field  $\vec{E}$  is established in a conductor, the charge carriers (assumed positive) acquire a **drift speed**  $v_d$  in the direction of  $\vec{E}$ ; the velocity  $\vec{v}_d$  is related to the current density by

$$\vec{J} = (ne)\vec{v}_d, \qquad (26-7)$$

where ne is the carrier charge density.

**Resistance of a Conductor** The resistance R of a conductor is defined as

$$R = \frac{V}{i} \qquad \text{(definition of } R\text{)},\tag{26-8}$$

where V is the potential difference across the conductor and i is the current. The SI unit of resistance is the **ohm**  $(\Omega)$ :  $1 \Omega = 1 \text{ V/A}$ . Similar equations define the **resistivity**  $\rho$  and **conductivity**  $\sigma$  of a material:

$$\rho = \frac{1}{\sigma} = \frac{E}{J} \qquad \text{(definitions of } \rho \text{ and } \sigma\text{)}, \tag{26-12,26-10)}$$

where E is the magnitude of the applied electric field. The SI unit of resistivity is the ohm-meter  $(\Omega \cdot m)$ . Equation 26-10 corresponds to the vector equation

$$\vec{E} = \rho \vec{J}. \tag{26-11}$$

The resistance R of a conducting wire of length L and uniform cross section is

$$R = \rho \frac{L}{A},\tag{26-16}$$

where A is the cross-sectional area.

**Change of \rho with Temperature** The resistivity  $\rho$  for most materials changes with temperature. For many materials, including metals, the relation between  $\rho$  and temperature T is approximated by the equation

 $\rho - \rho_0 = \rho_0 \alpha (T - T_0). \tag{26-17}$ 

Here  $T_0$  is a reference temperature,  $\rho_0$  is the resistivity at  $T_0$ , and  $\alpha$  is the temperature coefficient of resistivity for the material.

**Ohm's Law** A given device (conductor, resistor, or any other electrical device) obeys *Ohm's law* if its resistance R, defined by Eq. 26-8 as V/i, is independent of the applied potential difference V. A given *material* obeys Ohm's law if its resistivity, defined by Eq. 26-10, is independent of the magnitude and direction of the applied electric field  $\vec{E}$ .

**Resistivity of a Metal** By assuming that the conduction electrons in a metal are free to move like the molecules of a gas, it is possible to derive an expression for the resistivity of a metal:

$$\rho = \frac{m}{e^2 n \tau}.$$
 (26-22)

Here n is the number of free electrons per unit volume and  $\tau$  is the mean time between the collisions of an electron with the atoms of the metal. We can explain why metals obey Ohm's law by pointing out that  $\tau$  is essentially independent of the magnitude E of any electric field applied to a metal.

**Power** The power P, or rate of energy transfer, in an electrical device across which a potential difference V is maintained is

$$P = iV$$
 (rate of electrical energy transfer). (26-26)

**Resistive Dissipation** If the device is a resistor, we can write Eq. 26-26 as

$$P = t^2 R = \frac{V^2}{R}$$
 (resistive dissipation). (26-27,26-28)

In a resistor, electric potential energy is converted to internal thermal energy via collisions between charge carriers and atoms.

**Semiconductors** Semiconductors are materials that have few conduction electrons but can become conductors when they are doped with other atoms that contribute free electrons.

**Superconductors** Superconductors are materials that lose all electrical resistance at low temperatures. Recent research has discovered materials that are superconducting at surprisingly high temperatures.